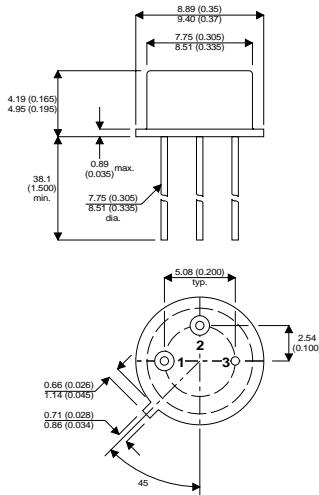


MECHANICAL DATA

Dimensions in mm



TO-5

Pin1 - Emitter

Pin2 - Base

Pin3 - Collector

**SMALL SIGNAL
PNP TRANSISTORS
IN TO-5**

APPLICATIONS

Low Power Silicon Alloy Junction PNP Transistors are specified for use in amplifier circuits.

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

V_{CB}	Collector – Base Voltage	25V
V_{CE}	Collector – Emitter Voltage	25V
V_{EB}	Emitter – Base Voltage	16V
I_{CM}	Collector Current	100mA
$I_{C(AV)}$	Collector Current ave Over any 20ms	50mA
I_{BM}	Base Current	50mA
$I_{B(AV)}$	Base Currentave Over any 20ms	15mA
I_{EM}	Emitter Current	100mA
$I_{E(AV)}$	Emitter Current ave Over any 20ms	65mA
F_{TOT}	Total Power Dissipation	250mA
T_{STG} , T_J	Operating and Storage Temperature	-53°C to +150°C

ELECTRICAL CHARACTERISTICS ($T_{\text{case}} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO} Collector Base Reverse Current	$V_{\text{CB}} = 6\text{V}$ $I_{\text{E}} = 0$			0.1	μA
	$V_{\text{CB}} = 6\text{V}$ $I_{\text{E}} = 0$ @100°C			5	
h_{fe} Small Signal Current Gain	$V_{\text{CE}} = 6\text{V}$ $I_{\text{C}} = 1\text{mA}$	25		60	—
f_{T} Transistion Frequency	$I_{\text{C}} = 1\text{mA}$ $V_{\text{CE}} = 6\text{V}$ $f = 300\text{kc/s}$	0.6			μA
NF Noise Figure	$I_{\text{C}} = 0.5\text{mA}$ $V_{\text{CE}} = 2\text{V}$ Z Source = 500 Ω			12	dB
$V_{\text{CE(SAT)}}$ Collector-Emitter Saturation Voltage	$I_{\text{C}} = 10\text{mA}$ $I_{\text{B}} = 1.5\text{mA}$			250	mV
V_{BE} Base Emitter Voltage	$V_{\text{CB}} = 5\text{V}$ $I_{\text{E}} = 10\text{mA}$			750	mV